

Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D $T_C = +25^\circ C$
100V	28mΩ @ $V_{GS} = 10V$	40A

Description

This MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

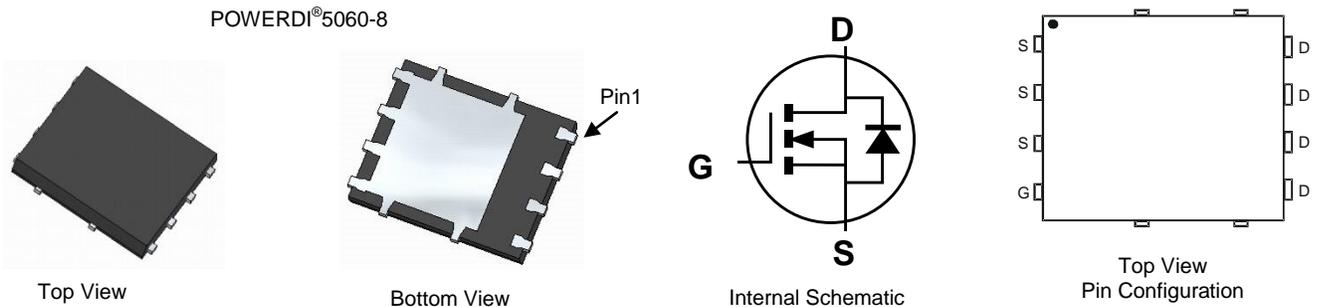
- Power Management Functions
- DC-DC Converters

Features

- Thermally Efficient Package-Cooler Running Applications
- High Conversion Efficiency
- Low $R_{DS(ON)}$ – Minimizes On State Losses
- Low Input Capacitance
- Fast Switching Speed
- <1.1mm Package Profile – Ideal for Thin Applications
- **Lead-Free Finish; RoHS compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. “Green” Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **An Automotive-Compliant Part is Available Under Separate Datasheet ([DMNH10H028SPSQ](#))**

Mechanical Data

- Case: POWERDI®5060-8
- Case Material: Molded Plastic, “Green” Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe Solderable per MIL-STD-202, Method 208 Ⓜ3
- Weight: 0.097 grams (Approximate)

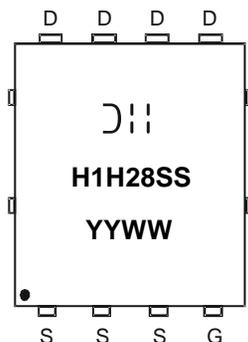


Ordering Information (Note 4)

Part Number	Case	Packaging
DMNH10H028SPS-13	POWERDI®5060-8	2500 / Tape & Reel

- Notes:
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



=Manufacturer's Marking
 H1H28SS = Product Type Marking Code
 YYWW = Date Code Marking
 YY = Last Two Digits of Year (ex: 15 = 2015)
 WW = Week Code (01 to 53)

Maximum Ratings (@T_C = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	100	V
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current, V _{GS} = 10V	Steady State	T _C = +25°C	I _D	40	A
		T _C = +100°C		25	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%) (Note 5)			I _{DM}	54	A
Maximum Continuous Body Diode Forward Current (Note 6)			I _S	3.9	A
Avalanche Current (Note 8) L=0.1mH			I _{AS}	26	A
Avalanche Energy (Note 8) L=0.1mH			E _{AS}	35	mJ

Thermal Characteristics

Characteristic			Symbol	Value	Unit
Total Power Dissipation (Note 5)			P _D	1.6	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady state		R _{θJA}	97	°C/W
Total Power Dissipation (Note 6)			P _D	2.9	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady state		R _{θJA}	52	°C/W
Thermal Resistance, Junction to Case			R _{θJC}	1.8	
Operating and Storage Temperature Range			T _J , T _{STG}	-55 to +175	°C

Electrical Characteristics (@T_C = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	100	—	—	V	V _{GS} = 0V, I _D = 250µA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1.0	µA	V _{DS} = 100V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	2.0	2.5	4.0	V	V _{DS} = V _{GS} , I _D = 250µA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	19	28	mΩ	V _{GS} = 10V, I _D = 20A
Diode Forward Voltage	V _{SD}	—	0.7	1.2	V	V _{GS} = 0V, I _S = 1.0A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	—	2245	—	pF	V _{DS} = 50V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oss}	—	173	—		
Reverse Transfer Capacitance	C _{rss}	—	68	—		
Gate Resistance	R _G	—	1.9	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz
Total Gate Charge (V _{GS} = 10V)	Q _g	—	36	—	nC	V _{DD} = 50V, I _D = 20A
Total Gate Charge (V _{GS} = 6.0V)	Q _g	—	22	—		
Gate-Source Charge	Q _{gs}	—	7.3	—		
Gate-Drain Charge	Q _{gd}	—	9.2	—		
Turn-On Delay Time	t _{D(ON)}	—	6.4	—	ns	V _{GS} = 10V, V _{DS} = 50V, R _G = 3.0Ω, I _D = 20A
Turn-On Rise Time	t _r	—	5.8	—		
Turn-Off Delay Time	t _{D(OFF)}	—	17.8	—		
Turn-Off Fall Time	t _f	—	4.8	—		
Reverse Recovery Time	t _{RR}	—	35	—	ns	I _F = 20A, di/dt = 100A/µs
Reverse Recovery Charge	Q _{RR}	—	47	—	nC	I _F = 20A, di/dt = 100A/µs

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

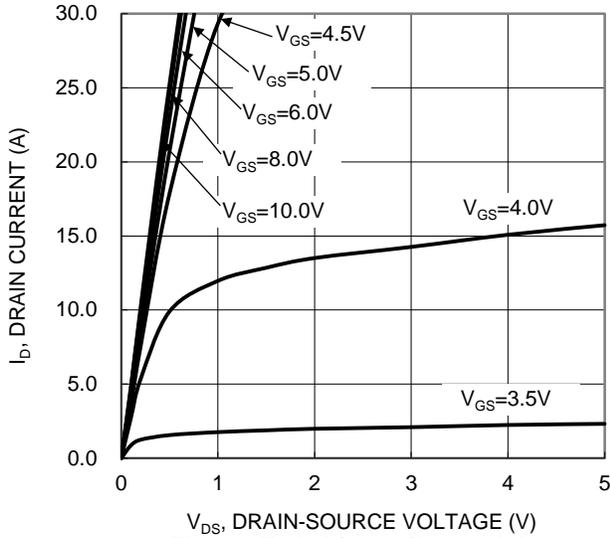


Figure 1. Typical Output Characteristic

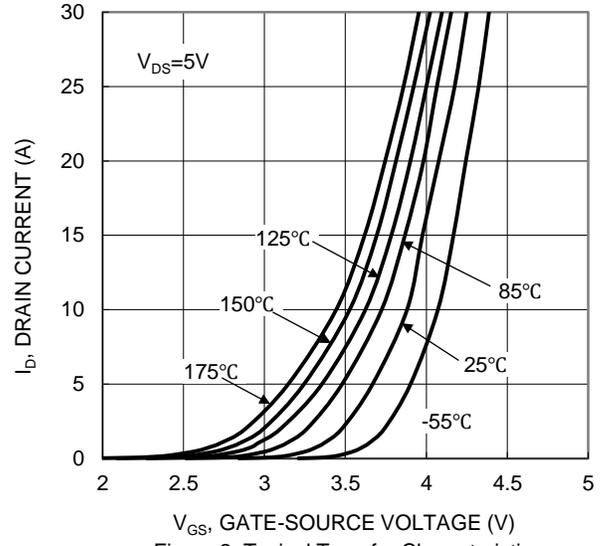


Figure 2. Typical Transfer Characteristic

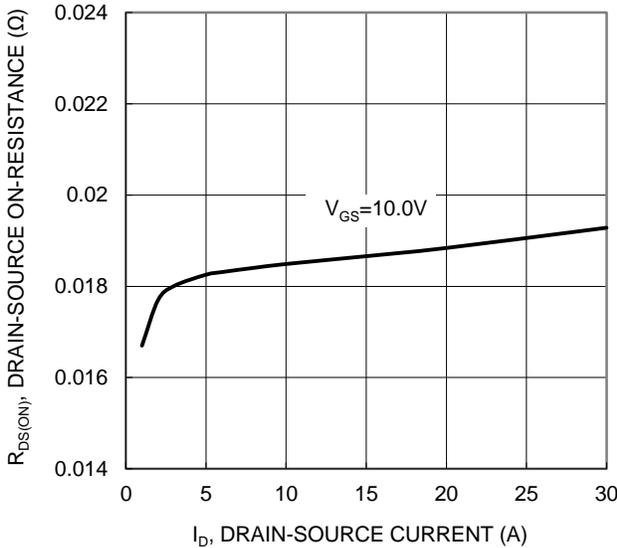


Figure 3. Typical On-resistance vs. Drain Current and Gate Voltage

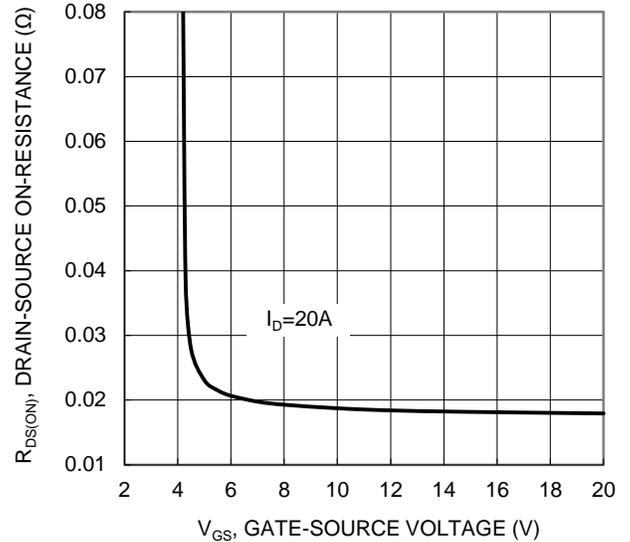


Figure 4. Typical Transfer Characteristic

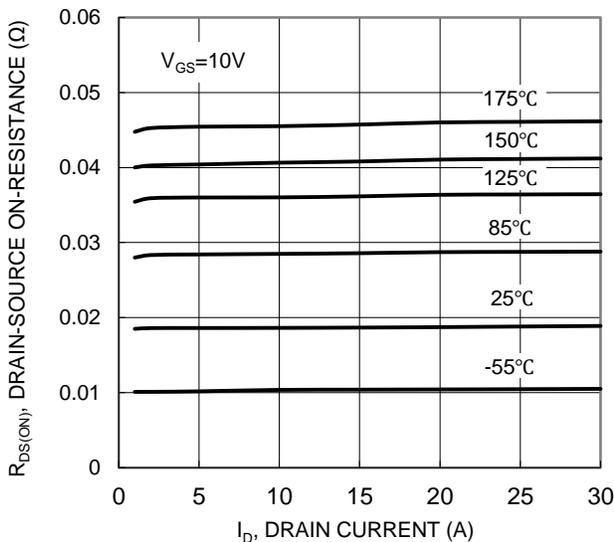


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

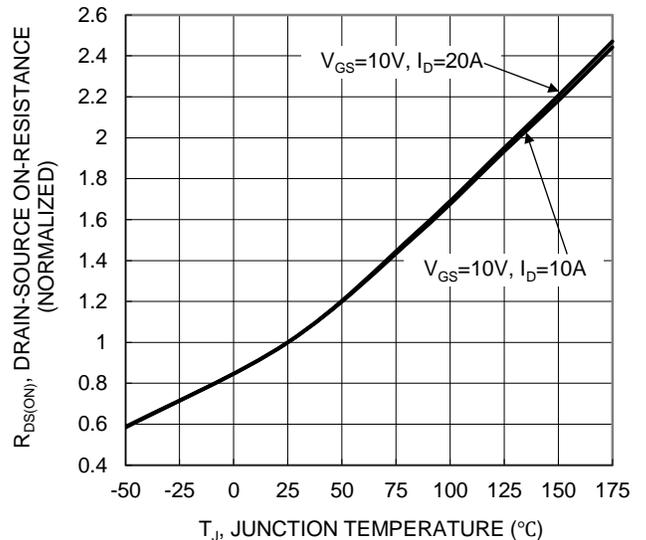


Figure 6. On-Resistance Variation with Temperature

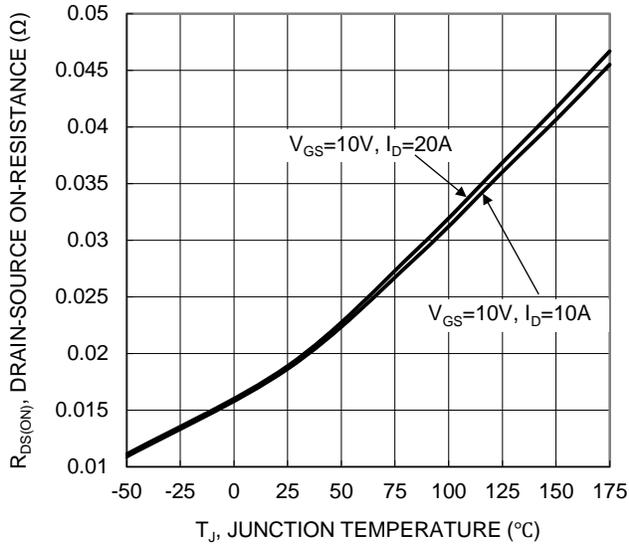


Figure 7. On-Resistance Variation with Temperature

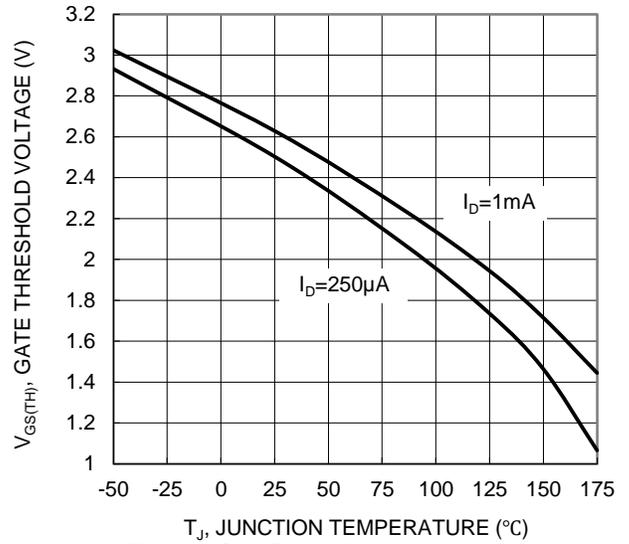


Figure 8. Gate Threshold Variation vs. Junction Temperature

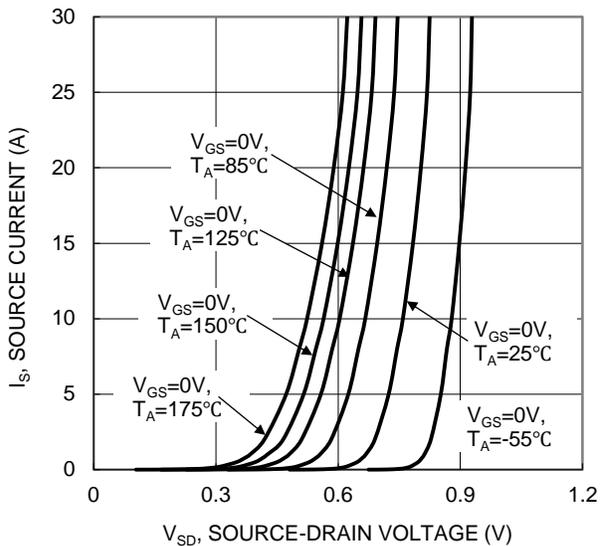


Figure 9. Diode Forward Voltage vs. Current

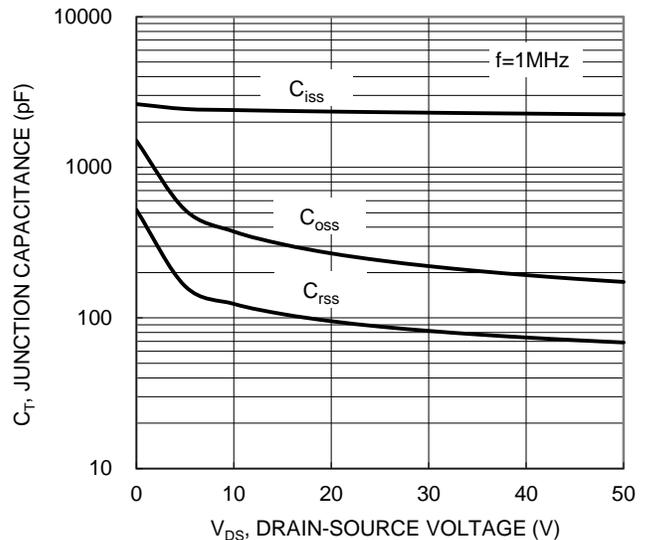


Figure 10. Typical Junction Capacitance

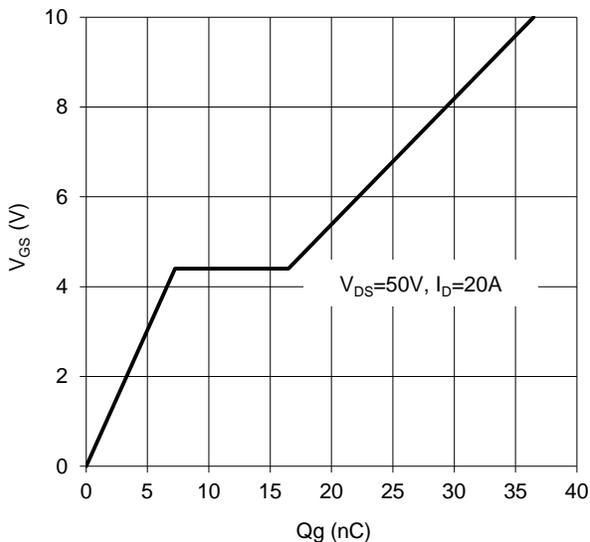


Figure 11. Gate Charge

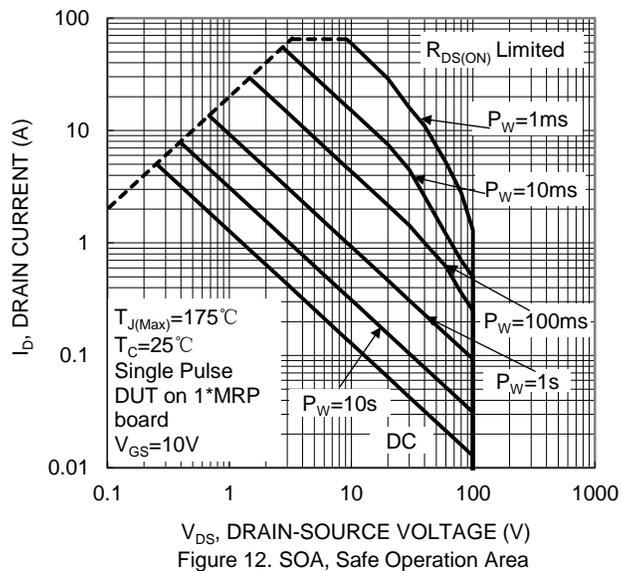


Figure 12. SOA, Safe Operation Area

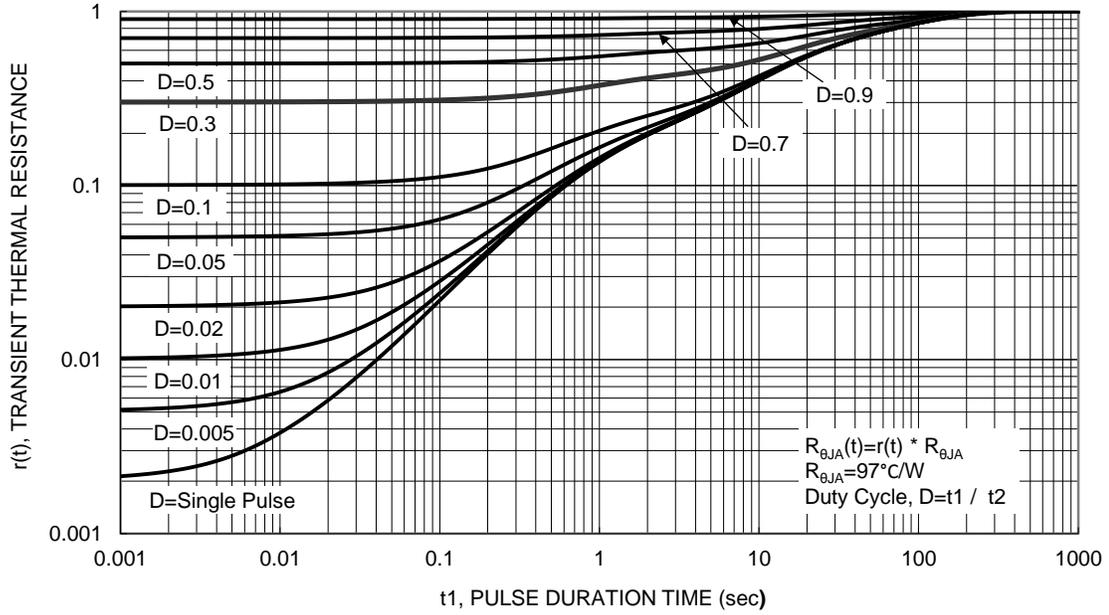
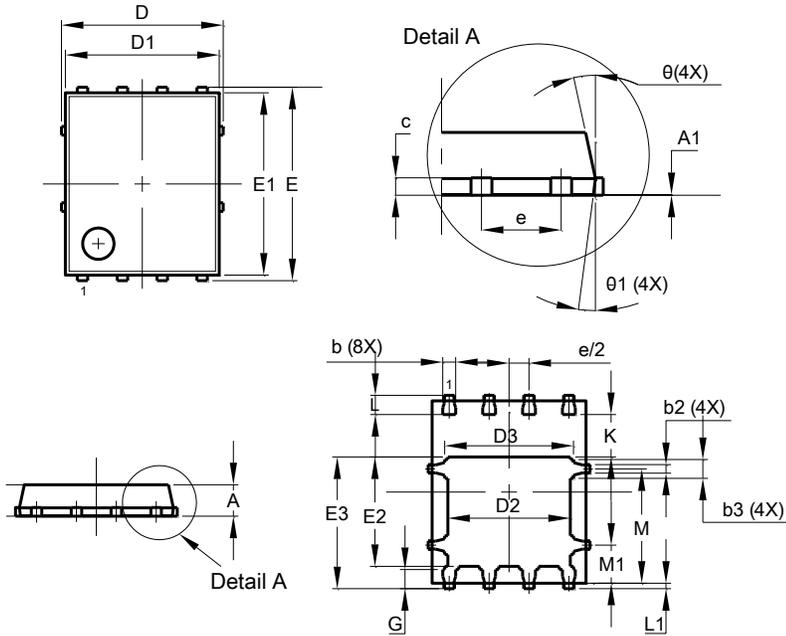


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

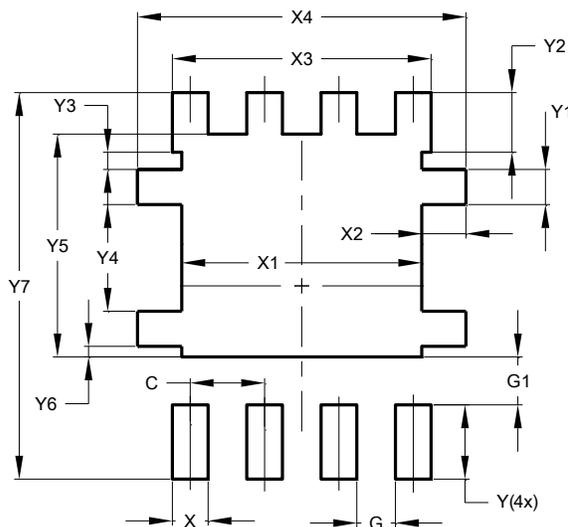
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



POWERDI [®] 5060-8			
Dim	Min	Max	Typ
A	0.90	1.10	1.00
A1	0.00	0.05	□
b	0.33	0.51	0.41
b2	0.200	0.350	0.273
b3	0.40	0.80	0.60
c	0.230	0.330	0.277
D	5.15 BSC		
D1	4.70	5.10	4.90
D2	3.70	4.10	3.90
D3	3.90	4.30	4.10
E	6.15 BSC		
E1	5.60	6.00	5.80
E2	3.28	3.68	3.48
E3	3.99	4.39	4.19
e	1.27 BSC		
G	0.51	0.71	0.61
K	0.51	□	□
L	0.51	0.71	0.61
L1	0.100	0.200	0.175
M	3.235	4.035	3.635
M1	1.00	1.40	1.21
θ	10°	12°	11°
θ1	6°	8°	7°
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
C	1.270
G	0.660
G1	0.820
X	0.610
X1	4.100
X2	0.755
X3	4.420
X4	5.610
Y	1.270
Y1	0.600
Y2	1.020
Y3	0.295
Y4	1.825
Y5	3.810
Y6	0.180
Y7	6.610

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